

KSD13003ER

KSU13003ER

SemiHow
Know-How for Semiconductor

KSD13003ER/KSU13003ER

High Voltage Switch Mode Application

- High Voltage, High Speed Switching
- Suitable for Switching regulator, Inverters motor controls
- 150°C Max. Operating temperature
- 8KV ESD proof at HBM (C=100pF, R=1.5kΩ)

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

 1.5 Amperes
 NPN Silicon Power Transistor
 25 Watts

| CHARACTERISTICS | SYMBOL | RATING | UNIT |
|---|-----------|---------|------------------|
| Collector-Base Voltage | V_{CBO} | 700 | V |
| Collector-Emitter Voltage | V_{CEO} | 400 | V |
| Emitter-Base Voltage | V_{EBO} | 9 | V |
| Collector Current(DC) | I_C | 1.5 | A |
| Collector Current(Pulse) | I_{CP} | 3 | A |
| Base Current | I_B | 0.75 | A |
| Collector Dissipation($T_C=25^\circ\text{C}$) | P_C | 25 | W |
| Storage Temperature | T_{STG} | -65~150 | $^\circ\text{C}$ |
| Max. Operating Junction Temperature | T_J | 150 | $^\circ\text{C}$ |

TO-252 / TO-251

1. Emitter
2. Collector
3. Base**D-PAK****I-PAK**

KSD13003ER K SU13003ER

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| CHARACTERISTICS | SYMBOL | Test Condition | Min | Typ. | Max | Unit |
|---------------------------------------|------------------------|---|--------|------|-------------------|---------------|
| Collector-Base Breakdown Voltage | V_{CBO} | $I_C=500\mu\text{A}, I_E=0$ | 700 | | | V |
| Collector-Emitter Breakdown Voltage | V_{CEO} | $I_C=1\text{mA}, I_B=0$ | 400 | | | V |
| Emitter Cut-off Current | I_{EBO} | $V_{EB}=9\text{V}, I_C=0$ | | | 10 | μA |
| *DC Current Gain | h_{FE1} h_{FE2} | $V_{CE}=10\text{V}, I_C=400\text{mA}$ $V_{CE}=10\text{V}, I_C=1.5\text{A}$ | 9 3 | | 38 | |
| *Collector-Emitter Saturation Voltage | $V_{CE}(\text{sat})$ | $I_C=0.5\text{A}, I_B=0.1\text{A}$ $I_C=1\text{A}, I_B=0.25\text{A}$ $I_C=1.5\text{A}, I_B=0.5\text{A}$ | | | 0.5 1.0 3.0 | V V V |
| *Base-Emitter Saturation Voltage | $V_{BE}(\text{sat})$ | $I_C=0.5\text{A}, I_B=0.1\text{A}$ $I_C=1\text{A}, I_B=0.25\text{A}$ | | | 1.0 1.2 | V V |
| Output Capacitance | C_{ob} | $V_{CB}=10\text{V}, f=0.1\text{MHz}$ | | 21 | | pF |
| Current Gain Bandwidth Product | f_T | $V_{CE}=10\text{V}, I_C=0.1\text{A}$ | 4 | | | MHz |
| Turn on Time | t_{on} | $V_{CC}=125\text{V}, I_C=2\text{A}$ $I_{B1}=0.2\text{A}, I_{B2}=-0.2\text{A}$ $R_L=125\Omega$ | | | 1.1 | μs |
| Storage Time | t_{stg} | | | | 4.0 | μs |
| Fall Time | t_F | | | | 0.7 | μs |

* Pulse Test: Pulse Widths $\leq 300\mu\text{s}$, Duty Cycles $\leq 2\%$

Note.

| hFE1 Classification | R | 15 ~ 25 |
|------------------------|---|---------|
| | O | 20 ~ 30 |
| | Y | 25 ~ 35 |

Package Mark information.

| S ER 13003 YWW Z | S | SemiHow Symbol |
|------------------------|-----|-----------------------------|
| | YWW | Y; year code, WW; week code |
| | Z | hFE1 Classification |

Typical Characteristics

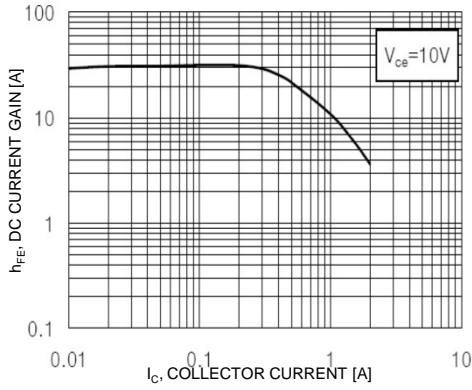


Figure 1. DC Current Gain

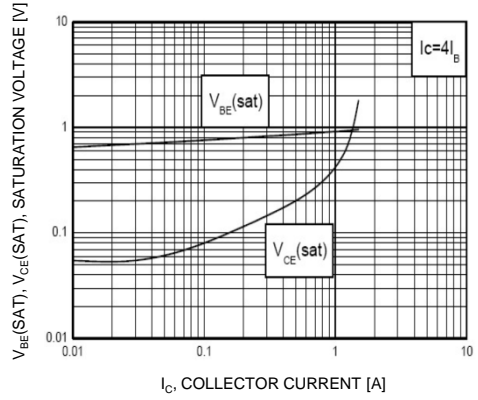


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

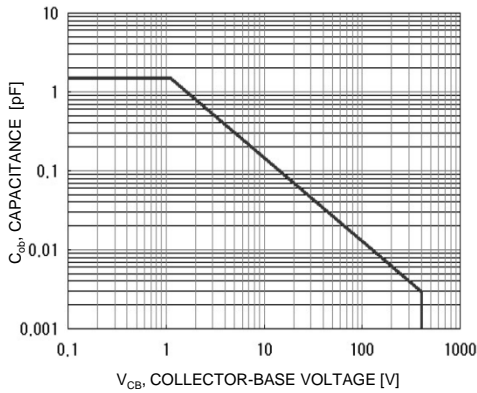


Figure 3. Forward Biased
Safe Operating Area

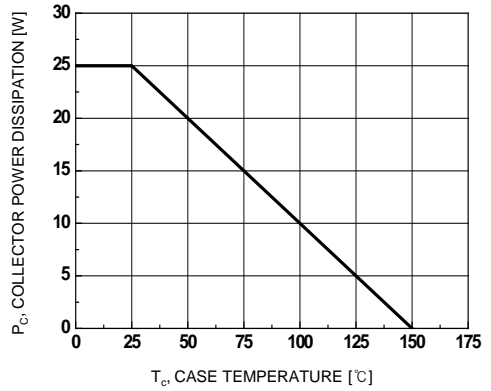
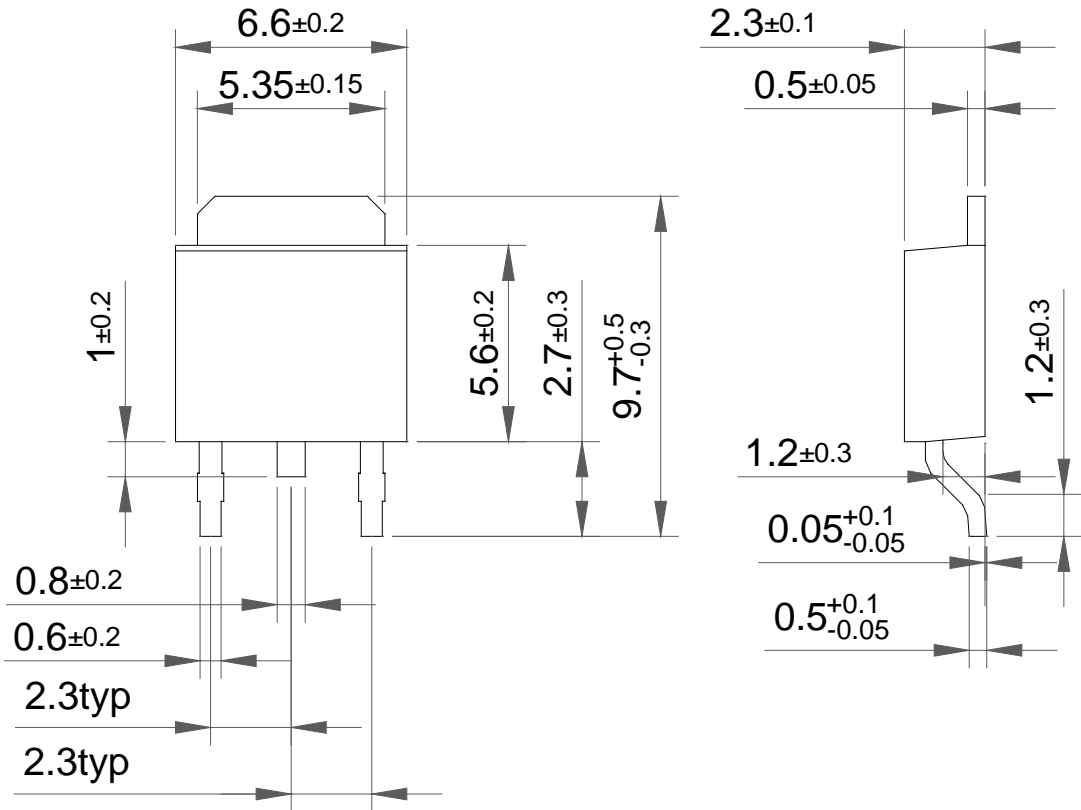


Figure 4. Power Derating

Package Dimension

TO-252



Package Dimension

TO-251

